

M54/74HC651 M54/74HC652

HC651 OCTAL BUS TRANSCEIVER/REGISTER (3-STATE, INV.) HC652 OCTAL BUS TRANSCEIVER/REGISTER (3-STATE)

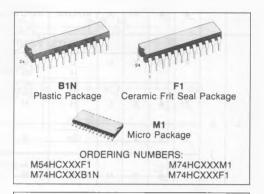
- LOW POWER DISSIPATION $I_{CC} = 4 \mu A$ (MAX.) at $T_A = 25^{\circ}C$
- HIGH NOISE IMMUNITY $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min)
- OUTPUT DRIVE CAPABILITY 15 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE |I_{OH}| = I_{OL} = 6 mA (MIN.)
- BALANCED PROPAGATION DELAYS tPLH = tPHL
- WIDE OPERATING VOLTAGE RANGE V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS651/652

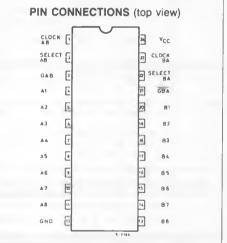
DESCRIPTION

M54/74HC651/652 are high speed CMOS OCTAL BUS TRANSCEIVERS AND REGISTERS (3-STATE), fabricated in silicon gate C²MOS technology. They have the same high speed performance of LSTTL combined with true CMOS low power consumption. These devices consist of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal storage registers. Enable GAB and GBA are provided to control the transceiver functions.

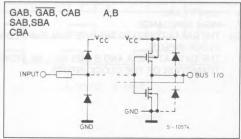
Select AB and Select BA control pins are provided to select whether real-time or stored data is transfered. A low input level selects real-time data, and a high selects stored data.

Data on the A or B bus, or both, can be stored in the internal D flip-flops by low-to-high transitions at the appropriate clock pins (CLOCK AB or CLOCK BA) regardless of the select or enable control pins. When select AB and select BA are in the real-time transfer mode, it is also possible to store data without using the internal D-type flip-flops by simultaneously enabling GAB and GBA. In this configuration each output reinforces its input. Thus, when all other data sources to the two sets of bus lines are at high impedance, each set of bus lines will remain at its last state. All inputs are equipped with protection circuits against static discharge and transient excess voltage.









M54/74HC651/652

TRUTH TABLE

M54/74HC652 (The truth table for M54/74HC651 is the same as this, but with the outputs inverted)

GAB	GBA	CAB	СВА	SAB	SBA	A	В	FUNCTION
						INPUTS	INPUTS	Both the A bus and the B bus are inputs.
		Х	Х	Х	Х	Z	Z	The output functions of the A and B bus are disabled
L	н	-	-	x	x	INPUTS	INPUTS	Both the A and B bus are used for inputs to the internal flip-flops. Data at the bus will be stored on low to high transition of the clock inputs.
						OUTPUTS	INPUTS	The A bus are outputs and the B bus are inputs.
		χ.	X	X	L	L H	L H	The data at the B bus are dipayed at the A bus.
L	L	X•	-	x	L	L H	L H	The data at the B bus are dispayed at the A bus. The data of the B bus are stored to the internal flip- flops on low to high transition of the clock pulse.
	L	Χ۰	x	x	н	Qn	x	The data stored to the internal flip-flops are dispayed at the A bus.
		X*	-	x	н	L H	L H	The data at the B bus are stored to the internal flip- flops on low to high transition of the clock pulse. The states of the internal flip-flops output directly to the A bus.
						INPUTS	OUTPUTS	The A bus are inputs and the B bus are outputs.
		x	X+	L	х	L H	L H	The data at the A bus are diplayed at the B bus.
н	н	-	X*	L	x	L H	L H	The data at the B bus are displayed at the A bus. The data of the B bus are stored to the internal flip- flops on low to high transition of the clock pulse.
п	п	x	Χ*	н	х	X	Qn	The data stored to the internal flip-flops are displayed at the B bus.
		F	X*	н	x	L H	L H	The data at the A bus are stored to the internal flip- flops on low to high transition of the clock pulse. The states of the internal flip-flops output directly to the B bus.
						OUTPUTS	OUTPUTS	Both the A bus and the B bus are outputs.
		x	x	н	н	Qn	Qn	The data stored to the internal flip-flops are displayed at the A and B bus respectively.
н	L	-	-	н	н	Qn	Qn	The output at the A bus are displayed at the B bus, the output at the B bus are displayed at the A bus respec

X : DON'T CARE.

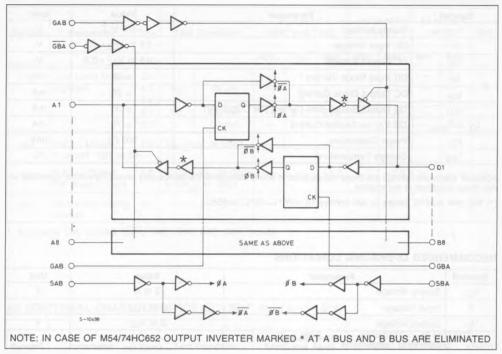
Z : HIGH IMPEDANCE.

Qn : THE DATA STORED TO THE INTERNAL FLIP-FLOPS BY MOST RECENT LOW TO HIGH TRANSITION OF THE CLOCK INPUTS.

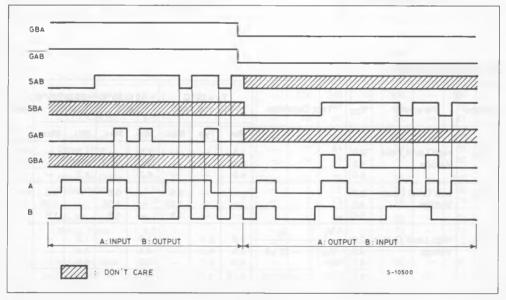
 THE DATA AT THE A AND B BUS WILL BE STORED TO THE INTERNAL FLIP-FLOPS ON EVERY LOW TO TRANSITION OF THE CLOCK INPUTS.



LOGIC DIAGRAM (HC652)



TIMING CHART



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to 7	V
VI	DC Input Voltage	- 0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	- 0.5 to V _{CC} + 0.5	V
lik	DC Input Diode Current	± 20	mA
lok	DC Output Diode Current	± 20	mA
IO	DC Output Source Sink Current Per Output Pin	± 35	mA
ICC or IGND	DC V _{CC} or Ground Current	± 70	mA
PD	Power Dissipation	500 (*)	mW
Tstg	Storage Temperature	- 65 to 150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≅ 65°C derate to 300 mW by 10 mW/°C: 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	V	/alue	Unit	
V _{CC}	Supply Voltage	2	to 6	V	
VI	Input Voltage	0 1	V		
Vo	Output Voltage	0 t	V		
T _A	Operating Temperature 74HC Series 54HC Series		- 40 to 85 - 55 to 125		
t _r , t _f	Input Rise and Fall Time	$V_{CC} \begin{pmatrix} 2 & V \\ 4.5V \\ 6 & V \end{pmatrix}$	0 to 1000 0 to 500 0 to 400	ns	

DC SPECIFICATIONS

Symbol	Parameter	v _{cc}	Test Condition		T _A = 25°C 54HC and 74HC			- 40 to 85°C 74HC		– 55 to 125°C 54HC		Unit
					Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
VIH	High Level Input Voltage	2.0 4.5 6.0			1.5 3.15 4.2		-	1.5 3.15 4.2	-	1.5 3.15 4.2	-	v
VIL	Low Level Input Voltage	2.0 4.5 6.0					0.5 1.35 1.8	-	0.5 1.35 1.8		0.5 1.35 1.8	v
V _{ОН}	High Level Output Voltage	4.5 6.0 4.5	V _I or V _{IL}	l ₀ - 20 μA - 6.0 mA	- 1.9 4.4 5.9 4.18	2.0 4.5 6.0 4.31	-	1.9 4.4 5.9 4.13	-	1.9 4.4 5.9 4.10	-	V
		4.5 6.0	VIL	– 6.0 mA – 7.8 mA	4.18 5.68	4.31 5.8	_	4.13 5.63	_	4.10 5.60	-	



DC SPECIFICATIONS (Continued)

Symbol	Parameter	Vcc	Test Condition		T _A = 25°C 54HC and 74HC				o 85°C HC	– 55 to 125°C 54HC		Unit
					Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{OL}	Low Level Output Voltage	2.0 4.5 6.0 4.5	V _{IH} or V _{IL}	20 µA		0 0 0	0.1 0.1 0.1 0.26		0.1 0.1 0.1 0.33		0.1 0.1 0.1 0.40	v
		6.0		7.8 mA	-	0.18	0.26	-	0.33	-	0.40	
I _{IN}	Input Leakage Current*	6.0	V _{IN} = V	CC or GND	_	_	± 0.1	-	±1	_	±1	
loz	3-State Output Off State Current	6.0		V _{CC} or GND _C or GND	-	-	±0.5	_	±0.5	-	± 10	μA
Icc	Quiescent Supply Current	6.0	V _I = V	CC or GND	_	-	4	-	40	-	80	

*: Applicable only to GAB, GBA, CAB, CBA, SAB, SBA, inputs.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

Symbol	Parameter	Vcc	Test Condition		A = 25° C and 3			o 85°C HC	– 55 to 125°C 54HC		Unit
				Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition Time	2.0 4.5 6.0		-	25 7 6	60 12 10		75 15 13		90 18 15	ns
t _{PLH} t _{PHL}	Propagation De- lay Time (BUS-BUS)	2.0 4.5 6.0		_	92 23 20	180 36 31	-	225 45 38	-	270 54 46	ns
t _{PLH} t _{PHL}	Propagation Delay Time (CLOCK-BUS)	2.0 4.5 6.0			124 31 26	240 48 41		300 60 51	-	360 72 61	ns
t _{PLH} t _{PHL}	Propagation Delay Time (SELECT-BUS)	2.0 4.5 6.0		-	112 28 24	220 44 37	_	275 55 47		330 66 56	ns
t _{W(H)} t _{W(L)}	Minimum Clock Pulse Width	2.0 4.5 6.0			30 8 7	75 15 13	-	95 19 16	_	110 22 19	ns
ts	Minimum Data Set-up Time	2.0 4.5 6.0			5 1 1	50 10 9		65 13 11	-	75 15 13	ns
th	Minimum Data Hold Time	2.0 4.5 6.0		_	_	25 5 5		30 6 5	_	40 8 7	ns



M54/74HC651/652

Symbol	Parameter	Vcc	Test Condition		A = 25° C and 7			o 85°C HC	– 55 to 125°C 54HC		Unit
				Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
tpzl tpzh	3-State Output Enable Time	2.0 4.5 6.0	$R_L = 1k\Omega$		100 25 21	180 36 31		225 45 38	-	270 54 46	ns
t _{PZL} t _{PZH}	3-State Output Disable Time	2.0 4.5 6.0	R _L = 1kΩ		88 22 19	170 34 29		215 43 37		255 51 43	ns
CIN	Input Capacitance			-	5	10	-	10	_	10	рF
C _{OUT}	Output Capacitance		BUS I/O	-	13	_	-	-	-	-	ρF
C _{PD} (*)	Power Dissipation Capacitance			-	46	-	_	=	_	_	

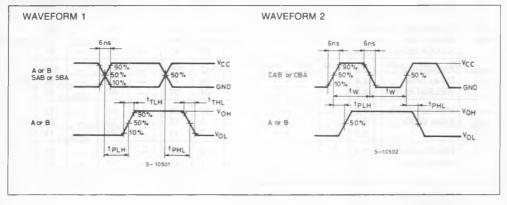
AC ELECTRICAL CHARACTERISTICS (Continued)

Note (*) C_{PD} is defined as the value of IC's internal equivalent capacitance which is calculated from the operating current consumption without load (refer to Test circuit).

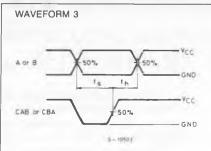
Average operating current can be obtained by equation hereunder.

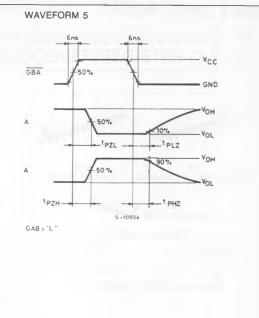
ICC(opr.) = CpD • VCC • fIN + ICC/8 (per bit)

SWITCHING CHARACTERISTICS TEST CIRCUIT AND WAVEFORM

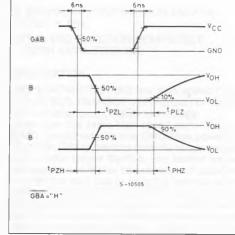


SWITCHING CHARACTERISTICS TEST CIRCUIT AND WAVEFORM (Continued)





WAVEFORM 4



TEST WAVEFORM ICC (Opr.)

